

RESEARCH OF TRANSFORMATION
OF MICRODEFECTS IN SILICON
AFTER IONIC IMPLANTATION

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S u m m a r y

With the purpose to study the interaction of dot defects formed in the process of ionic implantation with microdefects in silicon by electron microscopy, researches of dislocation-free silicon after ionic implantation of arsenic are carried out. Alloyed crystals were exposed to thermal treatment at 650 and 850 °. The received results testify to that, in the course of ionic implantation and following thermal treatment, the process of growth and transformation of microdefects against the background of disintegration of a solid solution silicon - arsenic occurs.